

## EconoPIM™3 module with TRENCHSTOP™ IGBT7 and emitter controlled 7 diode and NTC

### Features

- Electrical features
  - $V_{CES} = 1200\text{ V}$
  - $I_{C\text{nom}} = 150\text{ A} / I_{CRM} = 300\text{ A}$
  - TRENCHSTOP™ IGBT7
  - Overload operation up to  $175^\circ\text{C}$
  - Low  $V_{CE,\text{sat}}$
- Mechanical features
  - Integrated NTC temperature sensor
  - PressFIT contact technology
  - Copper base plate
  - $\text{Al}_2\text{O}_3$  substrate with low thermal resistance



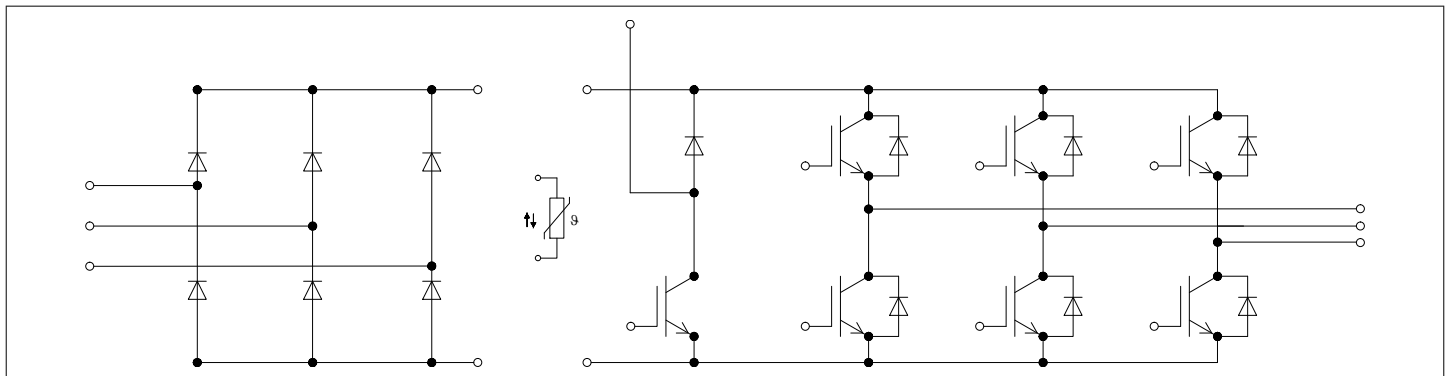
### Potential applications

- Auxiliary inverters
- Motor drives
- Servo drives

### Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

### Description



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## 1 Package

**Table 1** Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	$V_{ISOL}$	RMS, $f = 50 \text{ Hz}$ , $t = 1 \text{ min}$	2.5	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	$Al_2O_3$	
Creepage distance	$d_{Creep}$	terminal to heatsink	10.0	mm
Clearance	$d_{Clear}$	terminal to heatsink	7.5	mm
Comparative tracking index	$CTI$		> 200	
Relative thermal index (electrical)	$RTI$	housing	140	°C

**Table 2** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	$L_{SCE}$			25		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_C = 25^\circ\text{C}$ , per switch		1.1		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25^\circ\text{C}$ , per switch		1.6		mΩ
Storage temperature	$T_{stg}$		-40		125	°C
Mounting torque for module mounting	$M$	- Mounting according to valid application note		3	6	Nm
Weight	$G$			300		g

Note: The current under continuous operation is limited to 50 A rms per connector pin

## 2 IGBT, Inverter

**Table 3** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	$V_{CES}$	$T_{vj} = 25^\circ\text{C}$	1200	V
Continuous DC collector current	$I_{CDC}$	$T_{vj \text{ max}} = 175^\circ\text{C}$ $T_C = 80^\circ\text{C}$	150	A
Repetitive peak collector current	$I_{CRM}$	$t_p$ limited by $T_{vj \text{ op}}$	300	A
Gate-emitter peak voltage	$V_{GES}$		±20	V

**Table 4** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 150\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.55	1.80	V
			$T_{vj} = 125\ ^\circ C$		1.69		
			$T_{vj} = 175\ ^\circ C$		1.77		
Gate threshold voltage	$V_{GETh}$	$I_C = 3.5\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		5.15	5.80	6.45	V
Gate charge	$Q_G$	$V_{GE} = \pm 15\ V, V_{CE} = 600\ V$			2.5		$\mu C$
Internal gate resistor	$R_{Gint}$	$T_{vj} = 25\ ^\circ C$			1		$\Omega$
Input capacitance	$C_{ies}$	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			30.1		nF
Reverse transfer capacitance	$C_{res}$	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.105		nF
Collector-emitter cut-off current	$I_{CES}$	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			0.012	mA
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	$t_{don}$	$I_C = 150\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 3.3\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.172		$\mu s$
			$T_{vj} = 125\ ^\circ C$		0.183		
			$T_{vj} = 175\ ^\circ C$		0.189		
Rise time (inductive load)	$t_r$	$I_C = 150\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 3.3\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.072		$\mu s$
			$T_{vj} = 125\ ^\circ C$		0.077		
			$T_{vj} = 175\ ^\circ C$		0.080		
Turn-off delay time (inductive load)	$t_{doff}$	$I_C = 150\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 3.3\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.331		$\mu s$
			$T_{vj} = 125\ ^\circ C$		0.414		
			$T_{vj} = 175\ ^\circ C$		0.433		
Fall time (inductive load)	$t_f$	$I_C = 150\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 3.3\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.103		$\mu s$
			$T_{vj} = 125\ ^\circ C$		0.198		
			$T_{vj} = 175\ ^\circ C$		0.262		
Turn-on energy loss per pulse	$E_{on}$	$I_C = 150\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 3.3\ \Omega, di/dt = 1700\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		16.6		mJ
			$T_{vj} = 125\ ^\circ C$		24.9		
			$T_{vj} = 175\ ^\circ C$		29.6		
Turn-off energy loss per pulse	$E_{off}$	$I_C = 150\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 3.3\ \Omega, dv/dt = 3200\ V/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		10.4		mJ
			$T_{vj} = 125\ ^\circ C$		15.9		
			$T_{vj} = 175\ ^\circ C$		19.9		

(table continues...)

**Table 4 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
SC data	$I_{SC}$	$V_{GE} \leq 15 \text{ V}, V_{CC} = 800 \text{ V}, V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_p \leq 8 \mu\text{s}, T_{vj} = 150 \text{ }^\circ\text{C}$		520	A
			$t_p \leq 7 \mu\text{s}, T_{vj} = 175 \text{ }^\circ\text{C}$		490	
Thermal resistance, junction to case	$R_{thJC}$	per IGBT			0.290	K/W
Thermal resistance, case to heat sink	$R_{thCH}$	per IGBT, $\lambda_{grease} = 1 \text{ W}/(\text{m} \cdot \text{K})$		0.0680		K/W
Temperature under switching conditions	$T_{vj op}$		-40		175	$^\circ\text{C}$

Note:  $T_{vj op} > 150 \text{ }^\circ\text{C}$  is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

### 3 Diode, Inverter

**Table 5 Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	$V_{RRM}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	1200	V	
Continuous DC forward current	$I_F$		150	A	
Repetitive peak forward current	$I_{FRM}$	$t_p = 1 \text{ ms}$	300	A	
$I^2t$ - value	$I^2t$	$t_p = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ }^\circ\text{C}$	2700	$\text{A}^2\text{s}$
			$T_{vj} = 175 \text{ }^\circ\text{C}$	2250	

**Table 6 Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	$V_F$	$I_F = 150 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1.72	2.10	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1.59		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		1.52		
Peak reverse recovery current	$I_{RM}$	$V_R = 600 \text{ V}, I_F = 150 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 1700 \text{ A}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		65.3	A	
			$T_{vj} = 125 \text{ }^\circ\text{C}$		91.8		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		107		

(table continues...)

**Table 6 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Recovered charge	$Q_r$	$V_R = 600\text{ V}, I_F = 150\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 1700\text{ A}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$	10.3		$\mu\text{C}$
			$T_{vj} = 125\text{ }^\circ\text{C}$	21.7		
			$T_{vj} = 175\text{ }^\circ\text{C}$	28.6		
Reverse recovery energy	$E_{rec}$	$V_R = 600\text{ V}, I_F = 150\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 1700\text{ A}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$	3.27		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	7.32		
			$T_{vj} = 175\text{ }^\circ\text{C}$	9.88		
Thermal resistance, junction to case	$R_{thJC}$	per diode			0.463	K/W
Thermal resistance, case to heat sink	$R_{thCH}$	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$		0.0698		K/W
Temperature under switching conditions	$T_{vj\text{op}}$		-40		175	$^\circ\text{C}$

Note:  $T_{vj\text{op}} > 150\text{ }^\circ\text{C}$  is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

## 4 Diode, Rectifier

**Table 7 Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	$V_{RRM}$	$T_{vj} = 25\text{ }^\circ\text{C}$	1600	V	
Maximum RMS forward current per chip	$I_{FRMSM}$	$T_C = 100\text{ }^\circ\text{C}$	150	A	
Maximum RMS current at rectifier output	$I_{RMSM}$	$T_C = 100\text{ }^\circ\text{C}$	150	A	
Surge forward current	$I_{FSM}$	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ }^\circ\text{C}$	1600	A
			$T_{vj} = 150\text{ }^\circ\text{C}$	1400	
$I^2t$ - value	$I^2t$	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ }^\circ\text{C}$	12800	$\text{A}^2\text{s}$
			$T_{vj} = 150\text{ }^\circ\text{C}$	9800	

**Table 8 Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	$V_F$	$I_F = 150\text{ A}$		0.97		V
Reverse current	$I_r$	$T_{vj} = 150\text{ }^\circ\text{C}, V_R = 1600\text{ V}$		1		mA

(table continues...)

**Table 8 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	$R_{thJC}$	per diode			0.333	K/W
Thermal resistance, case to heat sink	$R_{thCH}$	per diode, $\lambda_{grease} = 1 \text{ W}/(\text{m}^*\text{K})$		0.0670		K/W
Temperature under switching conditions	$T_{vj, op}$		-40		150	°C

## 5 IGBT, Brake-Chopper

**Table 9 Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	$V_{CES}$	$T_{vj} = 25 \text{ °C}$	1200	V
Continuous DC collector current	$I_{CDC}$	$T_{vj max} = 175 \text{ °C}$ $T_C = 90 \text{ °C}$	100	A
Repetitive peak collector current	$I_{CRM}$	$t_p$ limited by $T_{vj op}$	200	A
Gate-emitter peak voltage	$V_{GES}$		±20	V

**Table 10 Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE sat}$	$I_C = 100 \text{ A}, V_{GE} = 15 \text{ V}$	$T_{vj} = 25 \text{ °C}$	1.50	1.80	V
			$T_{vj} = 125 \text{ °C}$	1.64		
			$T_{vj} = 175 \text{ °C}$	1.72		
Gate threshold voltage	$V_{GEth}$	$I_C = 2.5 \text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25 \text{ °C}$	5.15	5.80	6.45	V
Gate charge	$Q_G$	$V_{GE} = \pm 15 \text{ V}, V_{CE} = 600 \text{ V}$		1.8		µC
Internal gate resistor	$R_{Gint}$	$T_{vj} = 25 \text{ °C}$		1.5		Ω
Input capacitance	$C_{ies}$	$f = 100 \text{ kHz}, T_{vj} = 25 \text{ °C}, V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}$		21.7		nF
Reverse transfer capacitance	$C_{res}$	$f = 100 \text{ kHz}, T_{vj} = 25 \text{ °C}, V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}$		0.076		nF
Collector-emitter cut-off current	$I_{CES}$	$V_{CE} = 1200 \text{ V}, V_{GE} = 0 \text{ V}$ $T_{vj} = 25 \text{ °C}$			0.01	mA
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0 \text{ V}, V_{GE} = 20 \text{ V}, T_{vj} = 25 \text{ °C}$			100	nA

(table continues...)

**Table 10 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-on delay time (inductive load)	$t_{don}$	$I_C = 100\text{ A}, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 4.3\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C}$	0.169		$\mu\text{s}$
			$T_{vj} = 125\text{ }^\circ\text{C}$	0.180		
			$T_{vj} = 175\text{ }^\circ\text{C}$	0.187		
Rise time (inductive load)	$t_r$	$I_C = 100\text{ A}, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 4.3\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C}$	0.063		$\mu\text{s}$
			$T_{vj} = 125\text{ }^\circ\text{C}$	0.067		
			$T_{vj} = 175\text{ }^\circ\text{C}$	0.070		
Turn-off delay time (inductive load)	$t_{doff}$	$I_C = 100\text{ A}, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Goff} = 4.3\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C}$	0.310		$\mu\text{s}$
			$T_{vj} = 125\text{ }^\circ\text{C}$	0.390		
			$T_{vj} = 175\text{ }^\circ\text{C}$	0.410		
Fall time (inductive load)	$t_f$	$I_C = 100\text{ A}, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Goff} = 4.3\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C}$	0.110		$\mu\text{s}$
			$T_{vj} = 125\text{ }^\circ\text{C}$	0.190		
			$T_{vj} = 175\text{ }^\circ\text{C}$	0.250		
Turn-on energy loss per pulse	$E_{on}$	$I_C = 100\text{ A}, V_{CE} = 600\text{ V}, L_\sigma = 35\text{ nH}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 4.3\ \Omega, di/dt = 1100\text{ A}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$	7.12		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	11.7		
			$T_{vj} = 175\text{ }^\circ\text{C}$	14.5		
Turn-off energy loss per pulse	$E_{off}$	$I_C = 100\text{ A}, V_{CE} = 600\text{ V}, L_\sigma = 35\text{ nH}, V_{GE} = \pm 15\text{ V}, R_{Goff} = 4.3\ \Omega, dv/dt = 2800\text{ V}/\mu\text{s} (T_{vj} = 175\text{ }^\circ\text{C})$	$T_{vj} = 25\text{ }^\circ\text{C}$	6.93		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	10.6		
			$T_{vj} = 175\text{ }^\circ\text{C}$	13.3		
SC data	$I_{SC}$	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}, V_{CEmax} = V_{CES} - L_{sCE} * di/dt$	$t_p \leq 8\ \mu\text{s}, T_{vj} = 150\text{ }^\circ\text{C}$	370		A
			$t_p \leq 7\ \mu\text{s}, T_{vj} = 175\text{ }^\circ\text{C}$	350		
Thermal resistance, junction to case	$R_{thJC}$	per IGBT			0.373	K/W
Thermal resistance, case to heat sink	$R_{thCH}$	per IGBT, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$		0.0680		K/W
Temperature under switching conditions	$T_{vjop}$		-40		175	$^\circ\text{C}$

Note:  $T_{vjop} > 150\text{ }^\circ\text{C}$  is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.



## 6 Diode, Brake-Chopper

**Table 11** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	$V_{RRM}$	$T_{vj} = 25\text{ °C}$	1200	V	
Continuous DC forward current	$I_F$		50	A	
Repetitive peak forward current	$I_{FRM}$	$t_p = 1\text{ ms}$	100	A	
$I^2t$ - value	$I^2t$	$t_p = 10\text{ ms}, V_R = 0\text{ V}$	$T_{vj} = 125\text{ °C}$	220	A <sup>2</sup> s
			$T_{vj} = 175\text{ °C}$	200	

**Table 12** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	$V_F$	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$	1.72	2.10	V
			$T_{vj} = 125\text{ °C}$	1.59		
			$T_{vj} = 175\text{ °C}$	1.52		
Peak reverse recovery current	$I_{RM}$	$V_R = 600\text{ V}, I_F = 50\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 550\text{ A}/\mu\text{s} (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$	37.3		A
			$T_{vj} = 125\text{ °C}$	44.3		
			$T_{vj} = 175\text{ °C}$	49.6		
Recovered charge	$Q_r$	$V_R = 600\text{ V}, I_F = 50\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 550\text{ A}/\mu\text{s} (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$	3.86		$\mu\text{C}$
			$T_{vj} = 125\text{ °C}$	7.05		
			$T_{vj} = 175\text{ °C}$	10.1		
Reverse recovery energy	$E_{rec}$	$V_R = 600\text{ V}, I_F = 50\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 550\text{ A}/\mu\text{s} (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$	1.13		mJ
			$T_{vj} = 125\text{ °C}$	2.34		
			$T_{vj} = 175\text{ °C}$	3.23		
Thermal resistance, junction to case	$R_{thJC}$	per diode			0.909	K/W
Thermal resistance, case to heat sink	$R_{thCH}$	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^2\text{K})$		0.109		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note:  $T_{vj\text{ op}} > 150\text{ °C}$  is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

## 7 NTC-Thermistor

**Table 13** Characteristic values

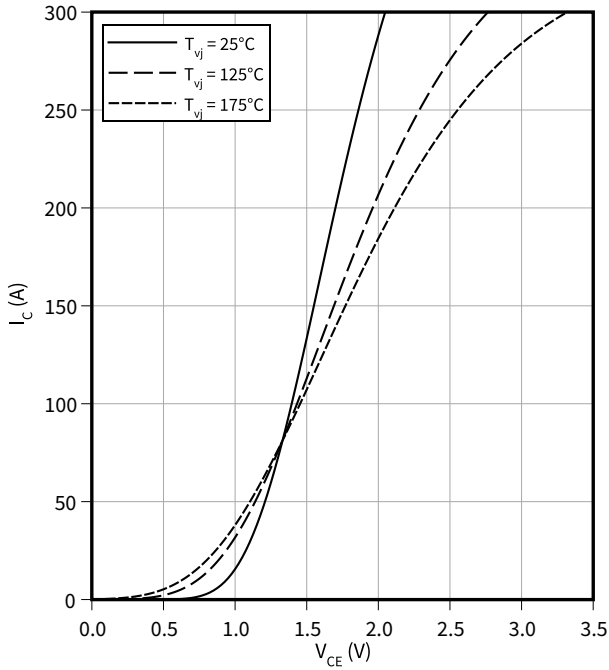
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	$R_{25}$	$T_{NTC} = 25\text{ °C}$		5		kΩ
Deviation of $R_{100}$	$\Delta R/R$	$T_{NTC} = 100\text{ °C}, R_{100} = 493\ \Omega$	-5		5	%
Power dissipation	$P_{25}$	$T_{NTC} = 25\text{ °C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$		3433		K

Note: Specification according to the valid application note.

## 8 Characteristics diagrams

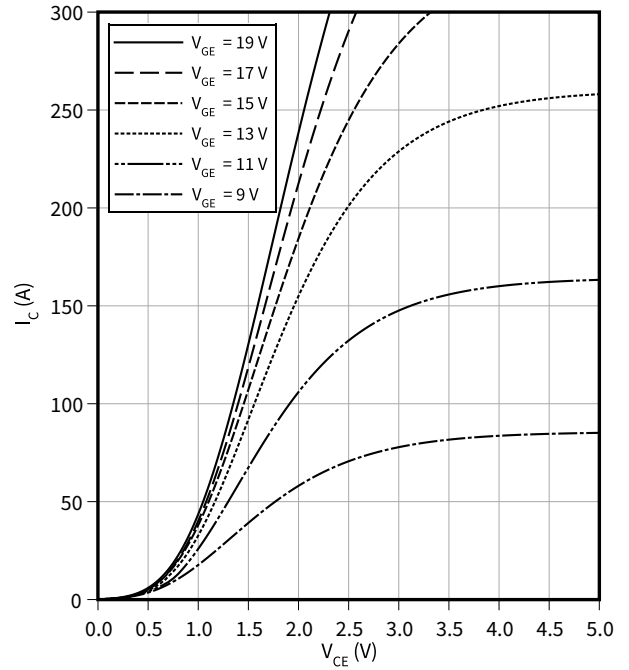
**Output characteristic (typical), IGBT, Inverter**

$I_C = f(V_{CE})$   
 $V_{GE} = 15 \text{ V}$



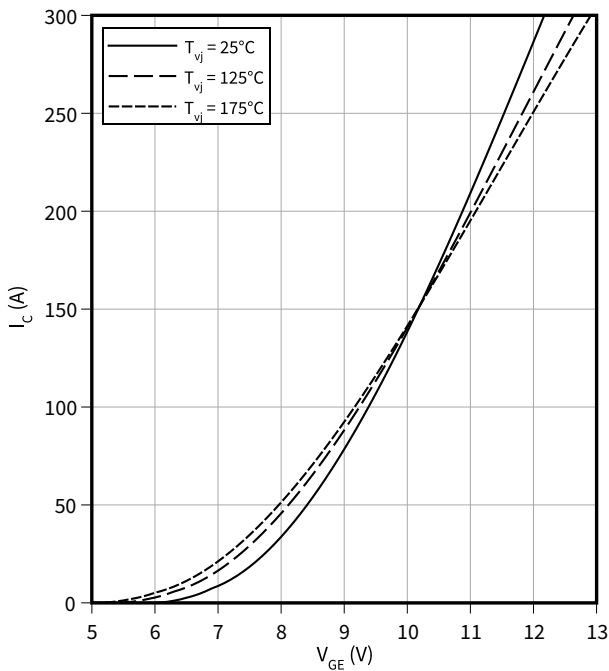
**Output characteristic field (typical), IGBT, Inverter**

$I_C = f(V_{CE})$   
 $T_{vj} = 175 \text{ °C}$



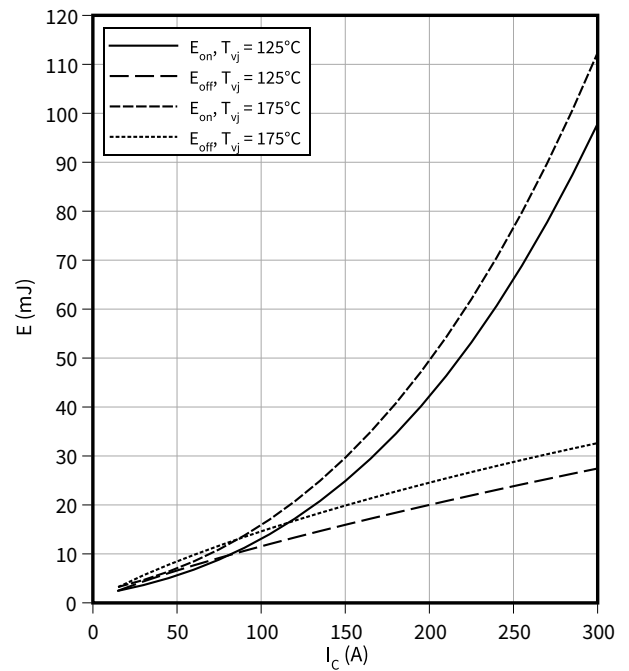
**Transfer characteristic (typical), IGBT, Inverter**

$I_C = f(V_{GE})$   
 $V_{CE} = 20 \text{ V}$



**Switching losses (typical), IGBT, Inverter**

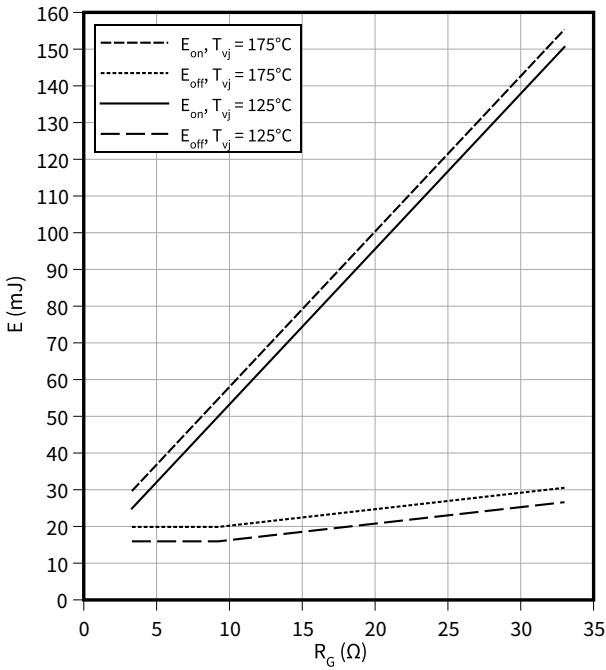
$E = f(I_C)$   
 $R_{Goff} = 3.3 \text{ } \Omega$ ,  $R_{Gon} = 3.3 \text{ } \Omega$ ,  $V_{GE} = \pm 15 \text{ V}$ ,  $V_{CE} = 600 \text{ V}$



**Switching losses (typical), IGBT, Inverter**

$E = f(R_G)$

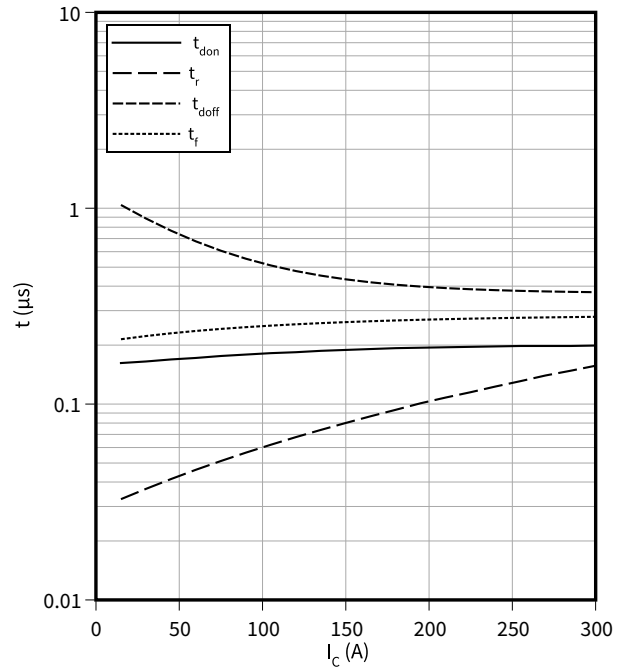
$V_{GE} = \pm 15 \text{ V}, I_C = 150 \text{ A}, V_{CE} = 600 \text{ V}$



**Switching times (typical), IGBT, Inverter**

$t = f(I_C)$

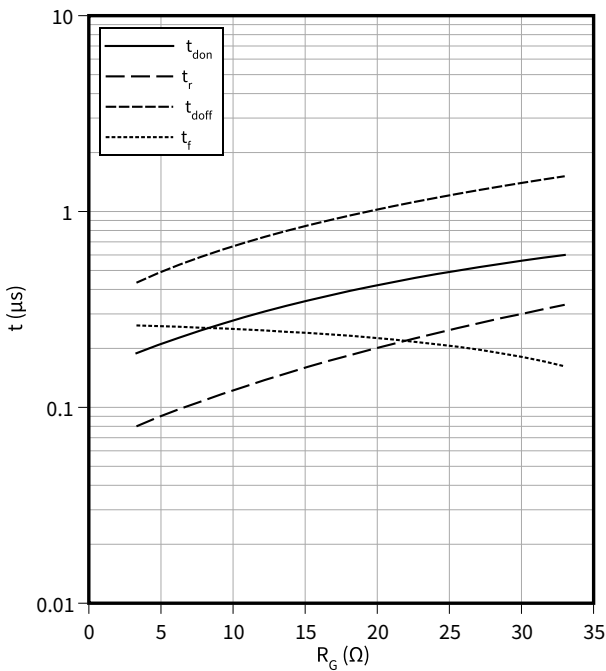
$R_{Goff} = 3.3 \Omega, R_{Gon} = 3.3 \Omega, V_{GE} = \pm 15 \text{ V}, V_{CE} = 600 \text{ V}, T_{vj} = 175 \text{ °C}$



**Switching times (typical), IGBT, Inverter**

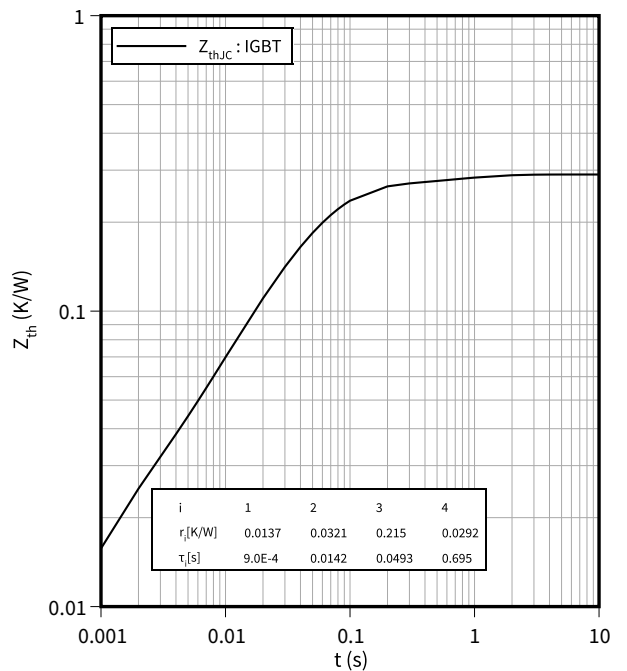
$t = f(R_G)$

$V_{GE} = \pm 15 \text{ V}, I_C = 150 \text{ A}, V_{CE} = 600 \text{ V}, T_{vj} = 175 \text{ °C}$



**Transient thermal impedance, IGBT, Inverter**

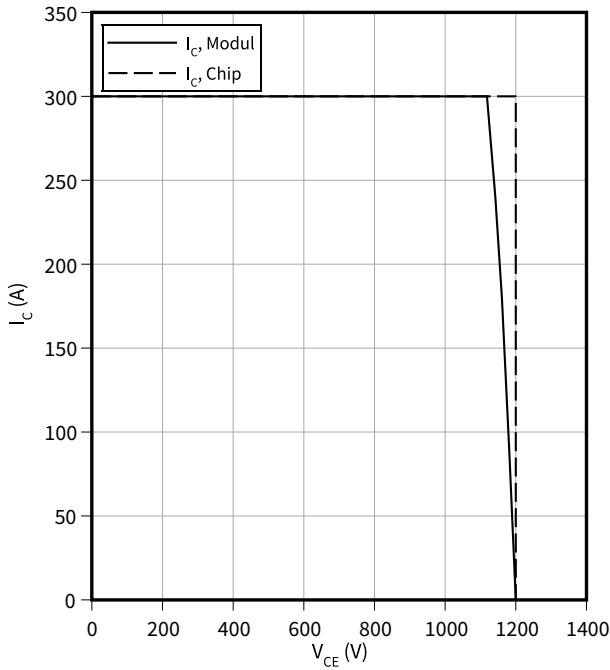
$Z_{th} = f(t)$



**Reverse bias safe operating area (RBSOA), IGBT, Inverter**

$I_C = f(V_{CE})$

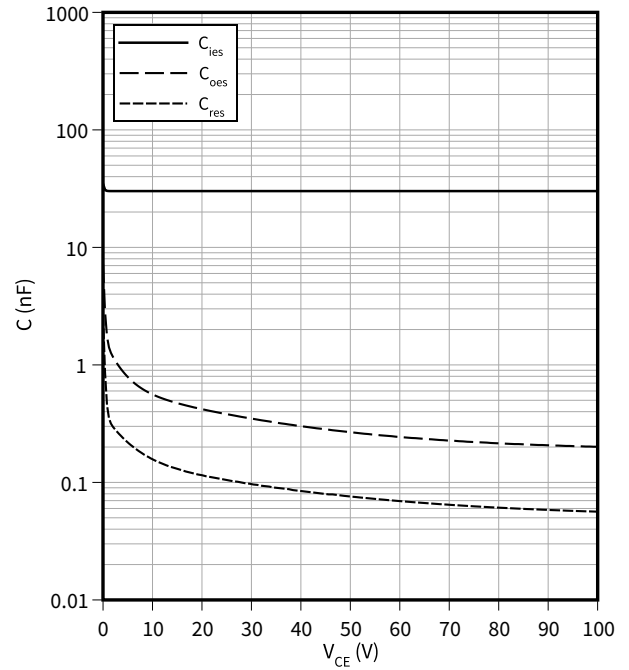
$R_{Goff} = 3.3 \Omega, V_{GE} = 15 V, T_{vj} = 175 \text{ }^\circ\text{C}$



**Capacity characteristic (typical), IGBT, Inverter**

$C = f(V_{CE})$

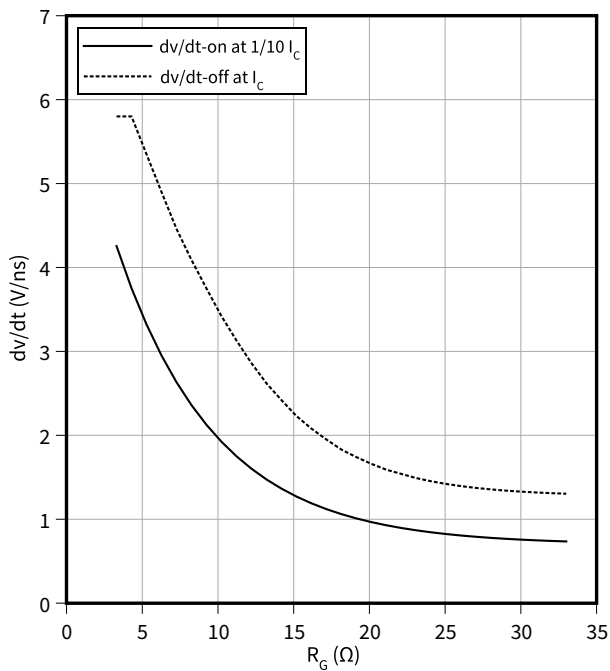
$f = 100 \text{ kHz}, V_{GE} = 0 V, T_{vj} = 25 \text{ }^\circ\text{C}$



**Voltage slope (typical), IGBT, Inverter**

$dv/dt = f(R_G)$

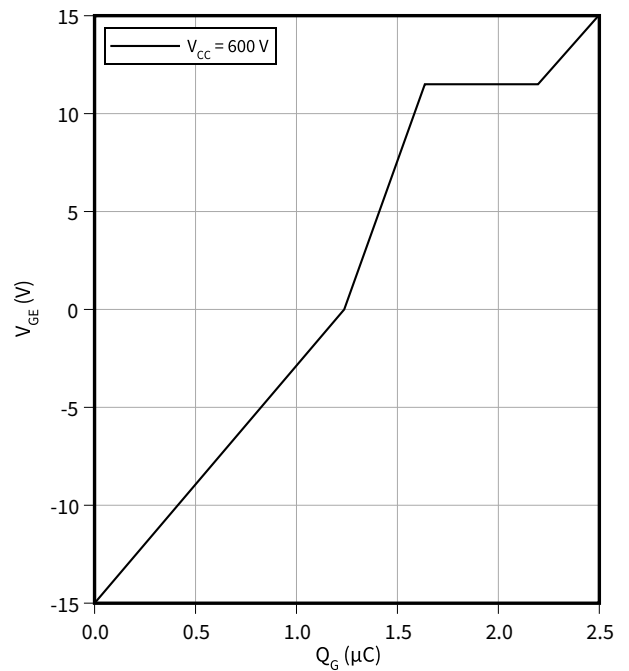
$I_C = 150 \text{ A}, V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 25 \text{ }^\circ\text{C}$



**Gate charge characteristic (typical), IGBT, Inverter**

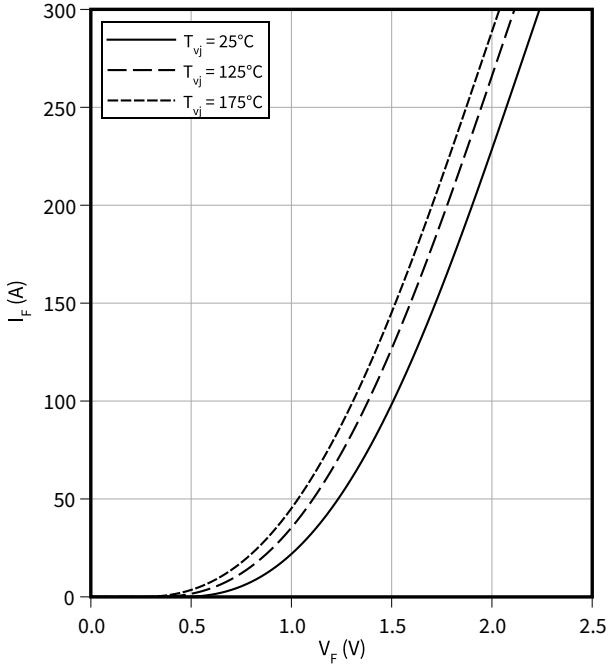
$V_{GE} = f(Q_G)$

$I_C = 150 \text{ A}, T_{vj} = 25 \text{ }^\circ\text{C}$



**Forward characteristic (typical), Diode, Inverter**

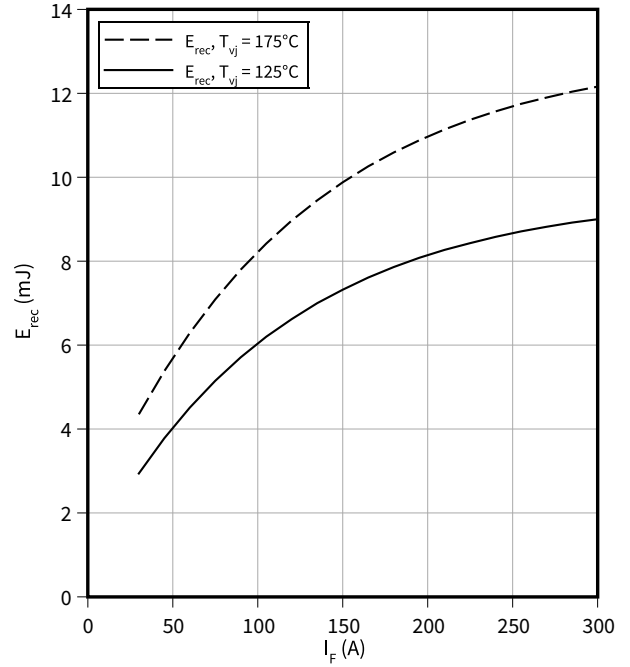
$I_F = f(V_F)$



**Switching losses (typical), Diode, Inverter**

$E_{rec} = f(I_F)$

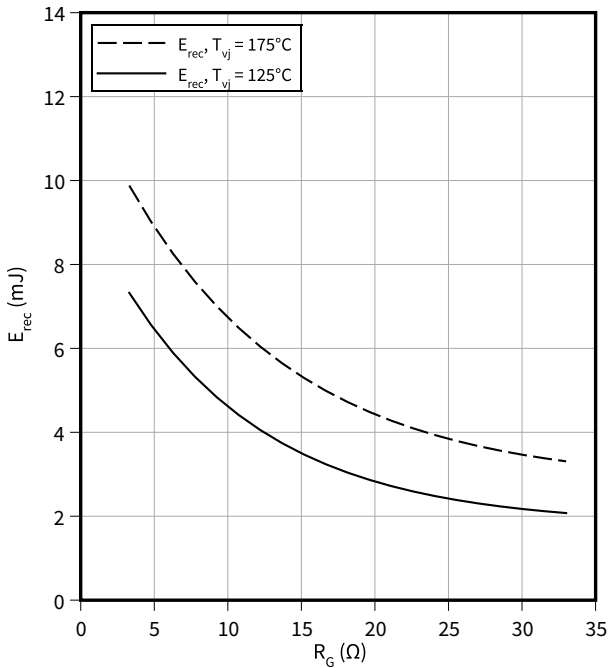
$R_{Gon} = 3.3 \Omega, V_{CE} = 600 \text{ V}$



**Switching losses (typical), Diode, Inverter**

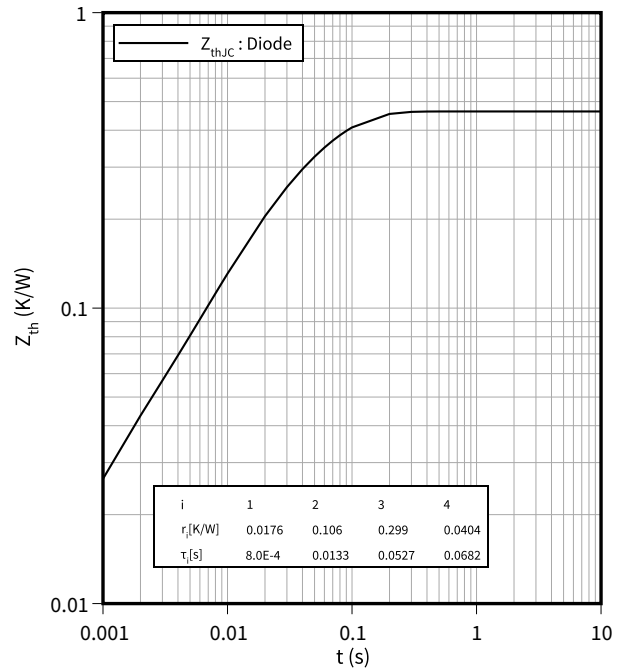
$E_{rec} = f(R_G)$

$V_{CE} = 600 \text{ V}, I_F = 150 \text{ A}$



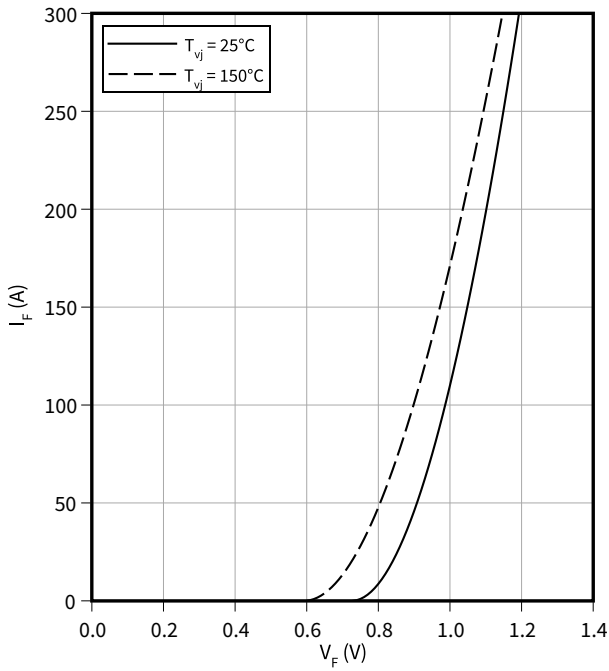
**Transient thermal impedance, Diode, Inverter**

$Z_{th} = f(t)$



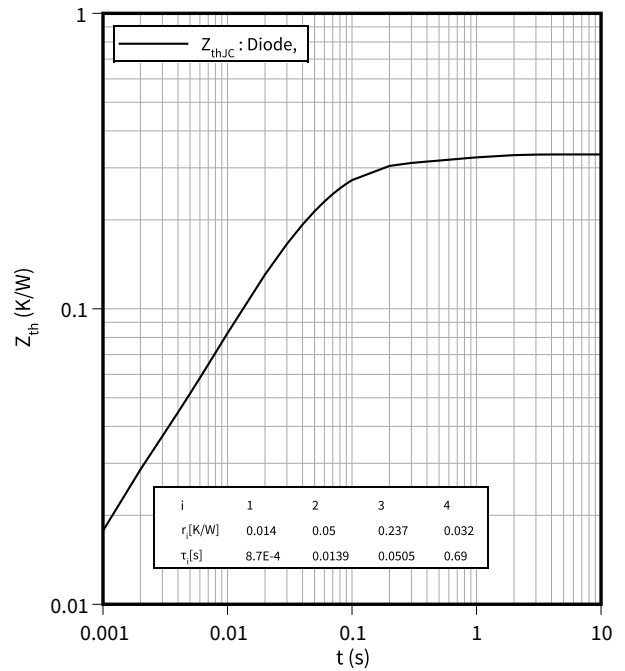
**Forward characteristic (typical), Diode, Rectifier**

$I_F = f(V_F)$



**Transient thermal impedance, Diode, Rectifier**

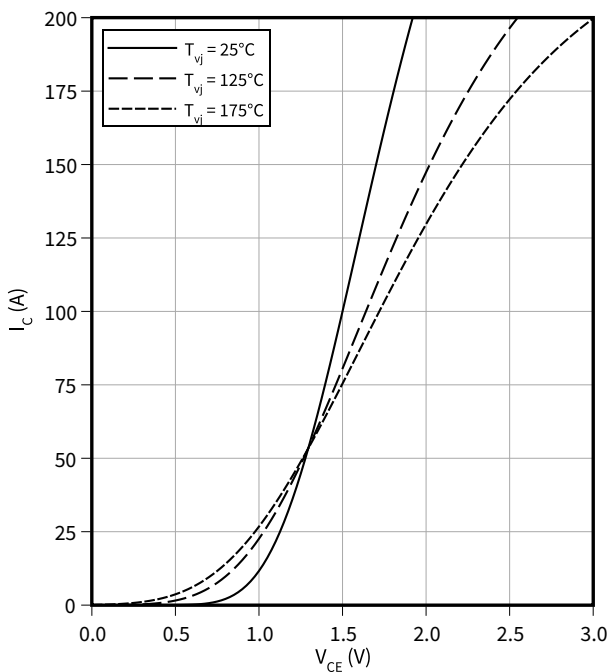
$Z_{th} = f(t)$



**Output characteristic (typical), IGBT, Brake-Chopper**

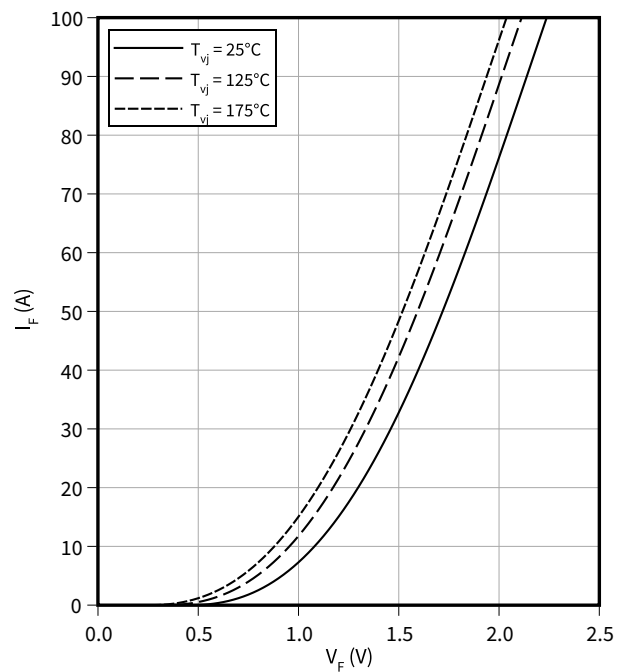
$I_C = f(V_{CE})$

$V_{GE} = 15 \text{ V}$



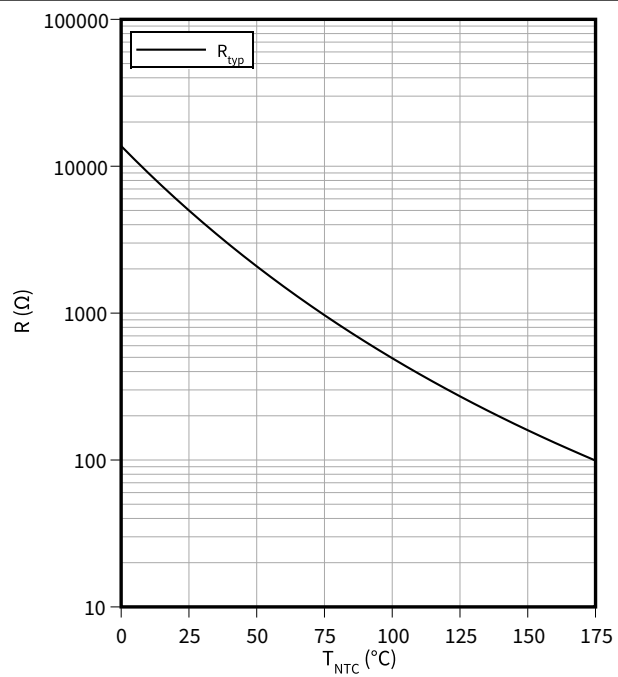
**Forward characteristic (typical), Diode, Brake-Chopper**

$I_F = f(V_F)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$





## 9 Circuit diagram

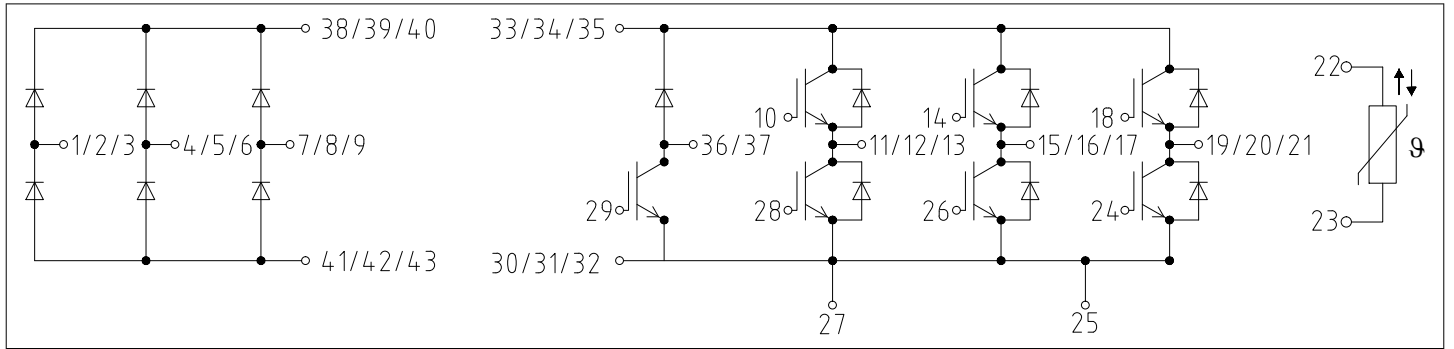


Figure 1

10 Package outlines

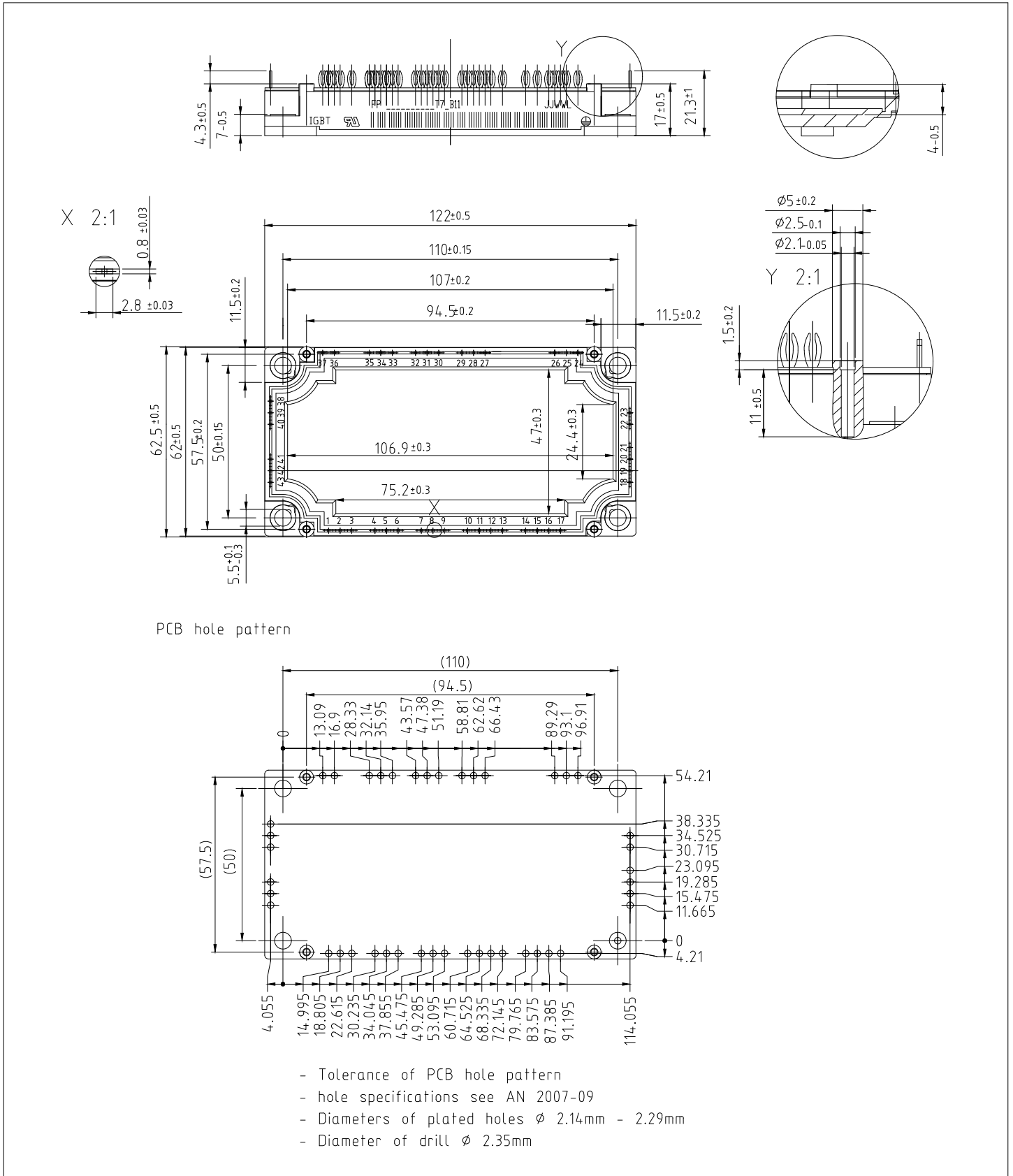


Figure 2

## 11 Module label code


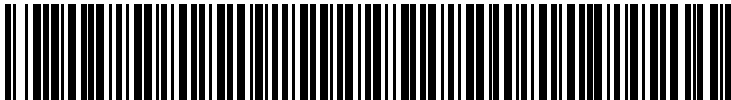
Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	<i>Content</i> Module serial number Module material number Production order number Date code (production year) Date code (production week)	<i>Digit</i> 1 - 5 6 - 11 12 - 19 20 - 21 22 - 23	<i>Example</i> 71549 142846 55054991 15 30
Example	 		
	71549142846550549911530		71549142846550549911530

Figure 3

## Revision history

Document revision	Date of release	Description of changes
0.10	2021-08-23	Initial version
1.00	2022-03-28	Final datasheet

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**Document reference**

**IFX-ABB764-002**

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